

Si Photo-diode Chip—TK0060PDN

1. Scope

- The specification applies to PIN silicon photo-diode chips.
- Type : TK0060PDN.

2. Structure

- PIN planar type.
- Electrode topside (anode) : Aluminum.
- Electrode backside (cathode) : Gold.

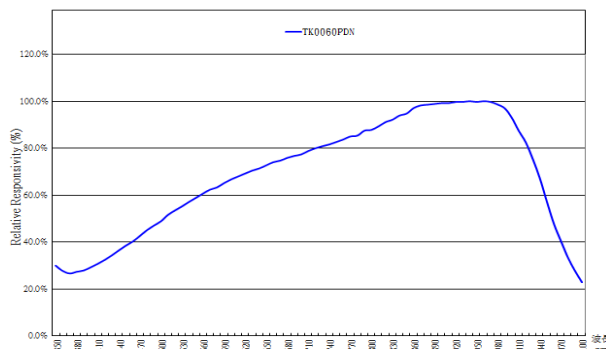
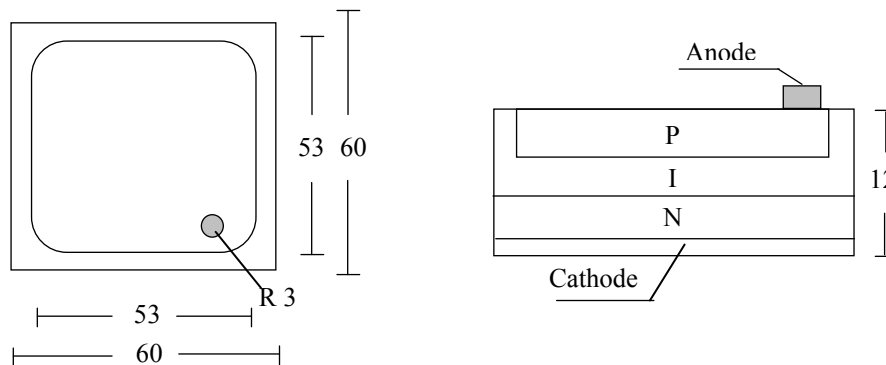
3. Size

- Chip size : 60mil × 60mil ± 1.5mil (1.520mm × 1.520mm ± 0.038mm)
- Thickness : 12mil ± 1mil (0.300mm ± 0.025mm)
- Active area : 53mil × 53mil ± 0.5mil (1.350mm × 1.350mm ± 0.013mm)
- Pad size : diameter 3mil ± 0.4mil (0.080mm ± 0.01mm)
- Pattern drawing : per fig. 1

4. Electro-Optical Characteristics

(Ta = +25 °C)

Parameter	Symbol	Condition	Min.	Typ.	Max.	Unit.
Forward Voltage	V_F	$I_F = 10\text{mA}$, $H=0$	0.5		1.3	V
Reverse Breakdown Voltage	V_{BR}	$I_R = 100\mu\text{A}$, $H=0$	35			V
Reverse Dark Current	I_D	$V_R = 10\text{V}$, $H=0$			10	nA
Light Current	I_L	$V_R = 5\text{V}$, H as $1\text{mw/cm}^2 @ 940\text{nm}$		55		μA
Peak Sensing Wavelength	λ_p			940		nm
Capacitance	C_J	$V_R = 3\text{V}$, $H=0$, $F=1\text{ MHz}$		11		pF



Unit : mil

fig. 1

2016.Mar



TYNTEK Head Office
 TYNTEK Chunan Branch
<http://www.tyntek.com.tw>

Tel : 886-3-5781616

Tel : 886-37-582997

E-mail : service@serv.tyntek.com.tw

Fax : 886-3-5780545

Fax : 886-37-582908